Atomistic Origins of Charge Traps in CdSe nanoclusters

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SUPPORTING INFORMATION

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Table S1 Globally optimized structures of Cd_nSe_m structures ($1 \le n, m \le 15$).





























Figure S1 Relative stability of Cd_nSe_m clusters expressed via lesser of two second-order differences: E(n, m + 1) + E(n, m - 1) - 2E(n, m) and E(n + 1, m) + E(n - 1, m) - 2E(n, m), where E(n, m) is a total energy of Cd_nSe_m cluster. As any cluster is globally unstable towards coalescence into the bulk, such a relative stability criteria are used



Figure S2 The structure, DOS and IPR = $1/N_{loc}(i)$ of the Cd₁₀Se₁₅ (a) and Cd₁₁Se₁₂ (b) clusters, corresponding to three stabilization stages





Table S2. Wavefunction, type and localization of strong and medium near-gap traps











